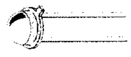
IREDS and PHOTOTRANSISTORS

Silonex packages IREDs and phototransistors in TO-46 flat and lensed window hermetic cans as well as open construction TO-46 can base where the chip is protected by epoxy encapsulation.

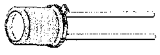
LED chip technologies include GaAlAs (880nm), GaAs (940nm) and Gap (700nm). In addition to our current phototransistors, Silonex has two larger area phototransistors in development.

- ...... ***Quality hermetic package***
- ...... ***"Can isolated" available***
- ...... ***Parameter selection available***
- ...... ***Building Block and Custom solutions available***

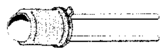
IRED package options



SLED-56E__



SLED-56HF__

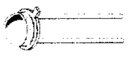


SLED-56HL__

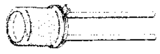
PART No.	**Output Power**	**Peak Wavelength**	**Forward Voltage**	**Reverse Breakdown**	**Reverse Current**
	I_F=50mA Min. (mW)	Typ. (nm)	I_F=60mA Max. (V)	I_R=10μA Min. (V)	V_R=3V Max. (μA)
SLED-56HL1	1.0	940	1.8	3	10
SLED-56HF1	1.0	940	1.8	3	10
SLED-56E1	1.0	940	1.8	3	10
SLED-56HL2	3.0	880	1.6	5	10
SLED-56HF2	3.0	880	1.6	5	10
SLED-56E2	3.0	880	1.6	5	10
SLED-56HL3	0.2 *	700	2.4 **	3	10
SLED-56HF3	0.2 *	700	2.4 **	3	10
SLED-56E3	0.2 *	700	2.4 **	3	10

*I_F=5mA **I_F=30mA

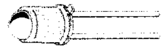
PTX package options



SLT-50E__



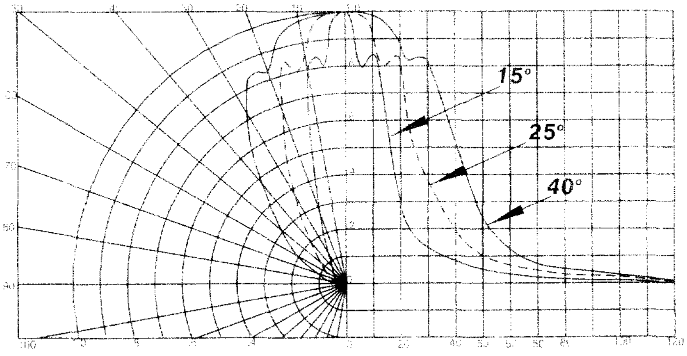
SLT-50HF__



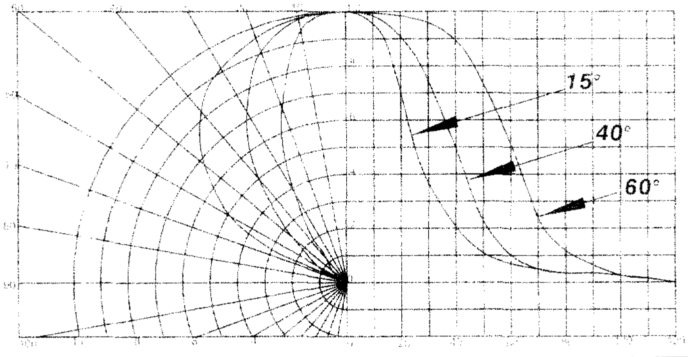
SLT-50HL__

PART No.	**Light Current**	**Dark Current**	**Collector Breakdown**	**Emitter Breakdown**	**Saturation Voltage**	**Rise/Fall Time**
	V_{CE}=5V (1) E_e=5mW/cm² Min. (mA)	V_{CE}=10V E_e=0 Max. (nA)	I_C=100μA E_e=0 Min. (V)	I_C=100μA E_e=0 Min. (V)	I_C=100mA I_B=0.5mA Max. (V)	I_C=0.8mA (2) R_L=100Ω Typ.(μsec)
SLT-50HF3	1.0	50	40	7.5	0.4	3
SLT-50HF4	2.5	50	40	7.5	0.4	3
SLT-50HL3	2.4	50	40	7.5	0.4	3
SLT-50HL4	4.0	50	40	7.5	0.4	3

(1) Light source is a frosted Tungsten incandescent Lamp @ 2854°K.
(2) Light source is a GaAs IRED with a Tr < 300ns.



TO-46 IRED Beam Emission Patterns



Sensor Directional Sensitivity Characteristics